



Product Summary

| V _{(BR)DSS} | Rds(on) max | Ι _D T _C = +25°C |
|----------------------|-----------------------------|---|
| -40V | $11m\Omega @ V_{GS} = -10V$ | -45A |
| -40 V | 15mΩ @ V_{GS} = -4.5V | -40A |

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Backlighting

175°C P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

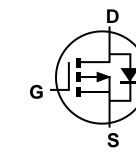
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



Top View



Equivalent Circuit

Ordering Information (Note 4)

| Part Number | Case | Packaging | | | |
|----------------|-------|-------------------|--|--|--|
| DMPH4015SK3-13 | TO252 | 2,500/Tape & Reel | | | |

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Top View

Pin-Out

G

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

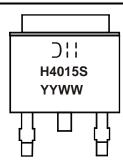
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



>!! = Manufacturer's Marking
H4015S = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 15 = 2015)
WW = Week (01 - 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

| Characteristic | Symbol | Value | Units | | |
|--|------------------|---|------------------|------------|----|
| Drain-Source Voltage | V _{DSS} | -40 | V | | |
| Gate-Source Voltage | | | V _{GSS} | ±25 | V |
| | Steady State | T _C = +25°C T _C = +100°C | ID | -45 -35 | А |
| Continuous Drain Current (Note 6) $V_{GS} = -10V$ | Steady State | T _A = +25°C T _A = +100°C | I _D | -14 -10 | A |
| Pulsed Drain Current (10μs pulse, duty cycle = 1%) | | | IDM | -100 | A |
| Maximum Body Diode Forward Current (Note 6) | | | Is | -5.5 | A |
| Avalanche Current, L = 1mH (Note 7) | | | I _{AS} | -22 | A |
| Avalanche Energy, L = 1mH (Note 7) | | | E _{AS} | 260 | mJ |

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Units | | |
|---|--------------|-----------------------------------|-------------|------|--|
| Total Power Dissipation (Note 5) | | PD | 1.7 | W | |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | $R_{	heta JA}$ | 73 | °C/W | |
| Total Power Dissipation (Note 6) | | PD | 3.3 | W | |
| Thermal Resistance, Junction to Ambient (Note 6) Steady State | | $R_{	heta JA}$ | 38 | °C/W | |
| Thermal Resistance, Junction to Case | | $R_{\theta JC}$ | 1.0 | C/VV | |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +175 | °C | |

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

| | | | _ | | | |
|---|---------------------|------|------|------|--------|--|
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
| OFF CHARACTERISTICS (Note 8) | | | 1 | 1 | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -40 | — | — | V | $V_{GS} = 0V, I_D = -250\mu A$ |
| Zero Gate Voltage Drain Current | IDSS | _ | | -1 | μA | $V_{DS} = -40V, V_{GS} = 0V$ |
| Gate-Source Leakage | I _{GSS} | _ | | ±100 | nA | $V_{GS} = \pm 25 V$, $V_{DS} = 0 V$ |
| ON CHARACTERISTICS (Note 8) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | -1.5 | -2 | -2.5 | V | $V_{DS} = V_{GS}, I_D = -250 \mu A$ |
| Static Drain-Source On-Resistance | | | 8 | 11 | mΩ | $V_{GS} = -10V, I_D = -9.8A$ |
| | R _{DS(ON)} | — | 11 | 15 | 1115.2 | $V_{GS} = -4.5V, I_D = -9.8A$ |
| Diode Forward Voltage | V _{SD} | _ | -0.7 | -1 | V | $V_{GS} = 0V, I_{S} = -1A$ |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | |
| Input Capacitance | C _{iss} | | 4234 | | | N 001/11/ 01/ |
| Output Capacitance | Coss | | 1036 | — | pF | V _{DS} = -20V, V _{GS} = 0V f = 1MHz |
| Reverse Transfer Capacitance | C _{rss} | — | 526 | — | | |
| Gate Resistance | Rg | _ | 7.8 | _ | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$ |
| Total Gate Charge (V _{GS} = -4.5V) | Qg | _ | 42.7 | _ | | |
| Total Gate Charge (V _{GS} = -10V) | Qg | | 91 | | -0 | V _{DS} = -20V, I _D = -9.8A |
| Gate-Source Charge | Q _{gs} | | 14.2 | | nC | |
| Gate-Drain Charge | Q _{gd} | | 13.5 | | | |
| Turn-On Delay Time | t _{D(ON)} | | 13.2 | | | |
| Turn-On Rise Time | t _R | | 10 | | | $\label{eq:VGS} \begin{array}{l} V_{GS} = \text{-}10V, \ V_{DD} = \text{-}20V, \\ R_G = 6\Omega, \ I_D = \text{-}1A \end{array}$ |
| Turn-Off Delay Time | t _{D(OFF)} | | 303 | | ns | |
| Turn-Off Fall Time | tF | | 138 | _ | 1 | |
| Reverse Recovery Time | t _{RR} | | 26 | | ns | I _F = -9.8A, di/dt = -100A/μs |
| Reverse Recovery Charge | Q _{RR} | | 20 | | nC | I _F = -9.8A, di/dt = -100A/µs |

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.

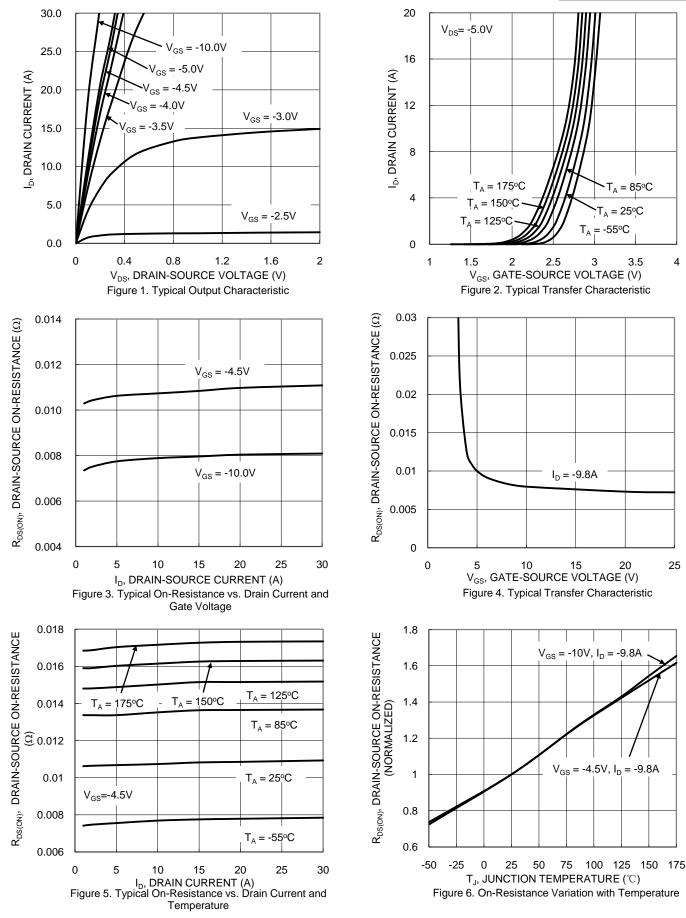
8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

NEW PRODUCT



DMPH4015SK3

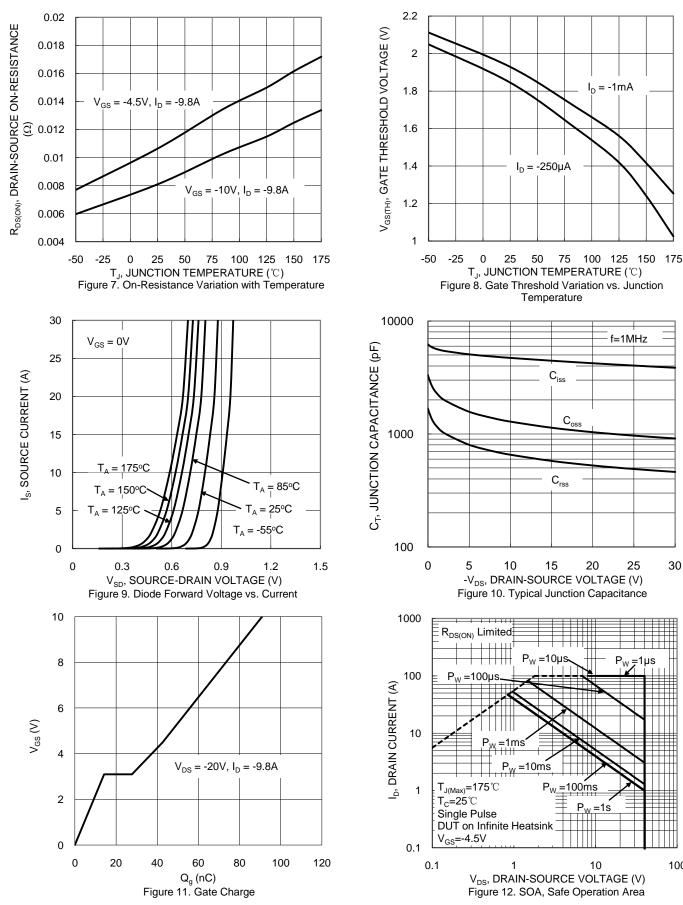


NEW PRODUCT

DMPH4015SK3 Document number: DS37425 Rev. 1 - 2



DMPH4015SK3



NEW PRODUCT

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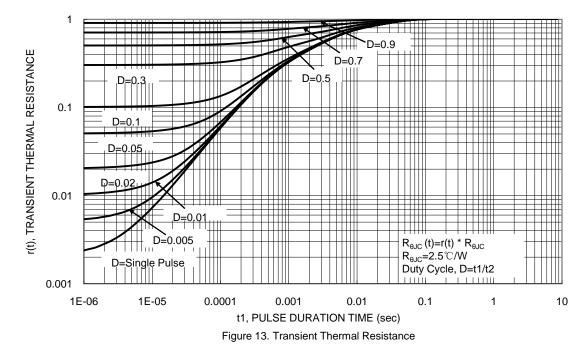
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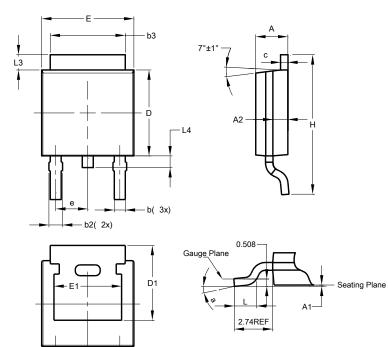




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

TO252 (DPAK)

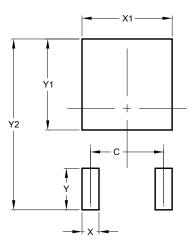


| TO252 (DPAK) | | | | | |
|--------------|----------------------|-------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 2.19 | 2.39 | 2.29 | | |
| A1 | 0.00 | 0.13 | 0.08 | | |
| A2 | 0.97 | 1.17 | 1.07 | | |
| b | 0.64 | 0.88 | 0.783 | | |
| b2 | 0.76 | 1.14 | 0.95 | | |
| b3 | 5.21 | 5.46 | 5.33 | | |
| С | 0.45 | 0.58 | 0.531 | | |
| D | 6.00 | 6.20 | 6.10 | | |
| D1 | 5.21 | - | - | | |
| е | - | - | 2.286 | | |
| Е | 6.45 | 6.70 | 6.58 | | |
| E1 | 4.32 | - | - | | |
| Н | 9.40 | 10.41 | 9.91 | | |
| L | 1.40 | 1.78 | 1.59 | | |
| L3 | 0.88 | 1.27 | 1.08 | | |
| L4 | 0.64 | 1.02 | 0.83 | | |
| а | 0° | 10° | - | | |
| All | All Dimensions in mm | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

TO252 (DPAK)



| Dimensions | Value (in mm) | | | |
|------------|---------------|--|--|--|
| С | 4.572 | | | |
| Х | 1.060 | | | |
| X1 | 5.632 | | | |
| Y | 2.600 | | | |
| Y1 | 5.700 | | | |
| Y2 | 10.700 | | | |



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